

SS9014

Pre-Amplifier, Low Level & Low Noise

- High total power dissipation. (P_T=450mW)
- High h_{FE} and good linearity
- Complementary to SS9015



1. Emitter 2. Base 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{CBO}	Collector-Base Voltage	50	V	
V _{CEO}	Collector-Emitter Voltage	45	V	
V _{EBO}	Emitter-Base Voltage	5	V	
I _C	Collector Current	100	mA	
P _C	Collector Power Dissipation	450	mW	
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Temperature	-55 ~ 150	°C	

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	50			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 1 \text{mA}, I_B = 0$	45			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 50 \text{V}, I_{E} = 0$			50	nA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			50	nA
h _{FE}	DC Current Gain	$V_{CE} = 5V$, $I_{C} = 1mA$	60	280	1000	
V _{CE} (sat)	Collector-Base Saturation Voltage	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$		0.14	0.3	
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$		0.84	1.0	V
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = 5V$, $I_{C} = 2mA$	0.58	0.63	0.7	V
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0 f=1MHz		2.2	3.5	pF
f _T	Current Gain Bandwidth Product	$V_{CE} = 5V$, $I_{C} = 10$ mA	150	270		MHz
NF	Noise Figure	V_{CE} =5V, I_{C} =0.2mA f=1KHz, R_{S} =2K Ω		0.9	10	dB

h_{FE} Classification

Classification	А	A B		D	
h _{FE}	60 ~ 150	100 ~ 300	200 ~ 600	400 ~ 1000	

Typical Characteristics

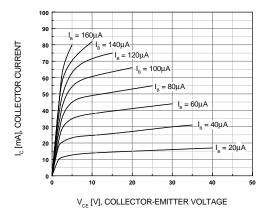
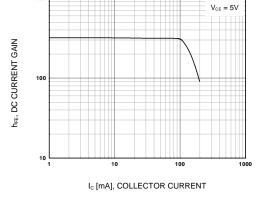


Figure 1. Static Characteristic



1000

Figure 2. DC current Gain

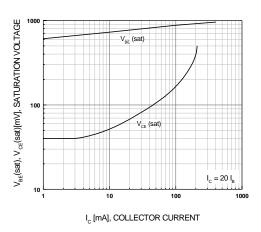


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

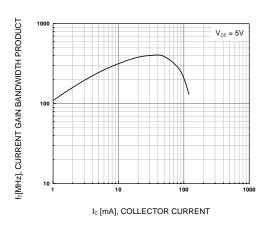
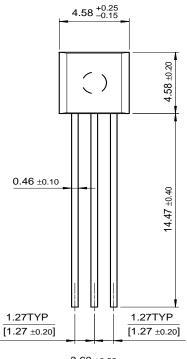
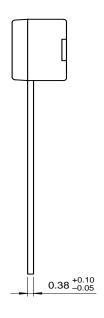


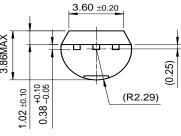
Figure 4. Current Gain Bandwidth Product

Package Demensions

TO-92







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